

**AMENDMENTS TO THE SPECIFICATION**

Please amend the fourth full paragraph in page 18 as follows:

Fig. 17 shows connection between the bit lines and the sense amplifiers in the memory cell array of this embodiment. Access word line AWL, refresh word line RWL and plate electrode PL connected to the cell plate are formed of the gate electrode layers at the same level, as shown in Fig. 16. When the access word line AWL is activated, the access sense amplifier is activated. When refresh word line RWL is activated, the refresh sense amplifier 41 is activated.

Please amend the paragraph spanning pages 20 and 21 as follows:

The refresh sense amplifiers 41a, 41b are operated similarly. For activating the refresh sense amplifiers on the opposite sides, the two refresh word lines RWL are activated. For activating only the refresh sense amplifier column on one side, only one refresh word line RWL is activated.